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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of

SUGIHARA ET AL.

Serial No. 10/560,907

Filed: December 16, 2005



Atty. Ref.: 1035-616

Group: 2131

Examiner: Unknown

For: SEMICONDUCTOR DEVICE, MANUFACTURING
METHOD THEREOF, AND ELECTRONIC DEVICE

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Commissioner for Patents
P. O. Box 1450
Alexandria, VA 22313-1450

Sir:

INFORMATION DISCLOSURE STATEMENT

As suggested by 37 C.F.R. 1.97, the undersigned attorney brings to the attention of the Patent and Trademark Office the references listed on the attached form PTO-1449.

- All listed documents are attached.
- Copies of U.S. Patent Publications are not required and are not attached.
- Listed foreign patent publications and other documents are enclosed.
- The partial translations were provided to the undersigned by the applicants' foreign representative. The undersigned has no knowledge regarding the pertinency of the partially translated portions vis-à-vis the document as a whole. The partial translations are merely provided for whatever convenience they may be.
- U.S. Patent 6,727,522 corresponds to the JP 2000-150900 reference and U.S. Patent 6,878,962 corresponds to the JP 2000-277534 reference.

This is not to be construed as a representation that a search has been made or that no better prior art exists, or that a reference is relevant merely because cited.

The Examiner is requested to initial the attached form PTO-1449 and to return a copy of the initialed document to the undersigned as an indication that the attached references have been considered and made of record.

The Commissioner is authorized to charge the undersigned's deposit account #14-1140 in whatever amount is necessary for entry of these papers and the continued pendency of the captioned application.

Respectfully submitted,
NIXON & VANDERHYE P.C.

July 26, 2006

By: H. Warren Burnam, Jr.
H. Warren Burnam, Jr.

Reg. No. 29,366

HWB:lsh
901 North Glebe Road, 11th Floor
Arlington, VA 22203-1808
Telephone: (703) 816-4000
Facsimile: (703) 816-4100



INFORMATION DISCLOSURE CITATION

ATTY. DOCKET NO.

SERIAL NO.

1035-616

JUL 26 2006

10/560,907

SUGIHARA ET AL.

(Use several sheets if necessary)

FILED DATE

GROUP

December 16, 2005

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U.S. PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS

OTHER DOCUMENTS (including Author, Title, Date, Pertinent pages, etc.)

	Hoffman et al, "ZnO-based transparent thin-film transistors", Applied Physics Letters, vol. 82, no. 5, 3 February 2003, pp.733-735
	Garcia et al, "Transparent ZnO thin-film transistor fabricated by rf magnetron sputtering", Applied Physics Letters, vol. 82, no. 7, 17 February 2203, pp. 1117-1119
	Nishii et al, "High Mobility Thin Film Transistors with Transparent ZnO Channels", Jpn. J. Appl. Phys., vol. 42, 2003, Part 2, no. 4A 1 April 2003 ©2003 The Japan Society of Applied Physics, pp. L347-L349

*Examiner

Date Considered

Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to application.

Form PTO-FB-A820 (Also PTO-1449)